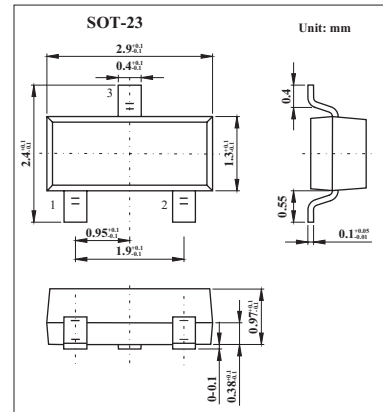


**MMBD1201;MMBD1203
MMBD1204;MMBD1205**

■ Features



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Working Inverse Voltage	W_{IV}	50	V
Average Rectified Current	I_o	200	mA
DC Forward Current	I_F	600	mA
Recurrent Peak Forward Current	i_f	700	mA
Peak Forward Surge Current	$i_f(\text{surge})$	1.0	A
Pulse width = 1.0 second		2.0	A
Pulse width = 1.0 microsecond			
Storage Temperature Range	T_{stg}	-55 to + 150	$^\circ\text{C}$
Operating Junction Temperature	T_J	150	$^\circ\text{C}$
Total Device Dissipation	P_D	350	mW
Derate above 25°C		2.8	mW / $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	$^\circ\text{C} / \text{W}$

**MMBD1201;MMBD1203
MMBD1204;MMBD1205**

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Breakdown voltage	B _V	I _R = 100 μA	100		V
Reverse current	I _R	I _F = 20 V		25	nA
		I _F = 50 V		50	nA
		I _F = 50 V, T _A = 150 °C		5	μA
Forward voltage	V _F	I _F = 1.0 mA	550	600	mV
		I _F = 10 mA	660	740	mV
		I _F = 100 mA	820	920	mV
		I _F = 200 mA	0.87	1.0	V
		I _F = 300 mA		1.1	V
Diode capacitance	C _D	V _R = 0, f = 1.0 MHz		2.0	pF
Reverse recovery time	T _{RR}	I _F = I _R = 10 mA, I _{RR} = 1.0 mA, R _L = 100 Ω		4.0	ns

■ Marking

Type	MMBD1201	MMBD1203	MMBD1204	MMBD1205
Marking	24	26	27	28